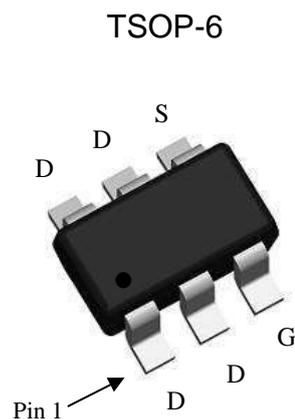


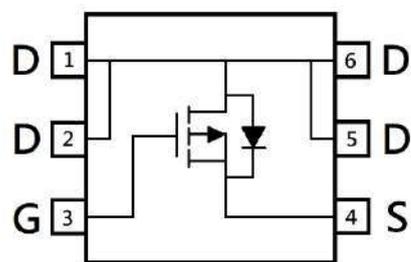
## P-Channel Enhancement Mode Power MOSFET

### Features :

- Low On Resistance
- Low Gate Charge
- Fast Switching Characteristic



$BV_{DSS}$	-20V
$I_D @ V_{GS} = -4.5V, T_A = 25^\circ C$	-3.9A
$R_{DS(ON)}$ typ. @ $V_{GS} = -4.5V, I_D = -4A$	42m $\Omega$
$R_{DS(ON)}$ typ. @ $V_{GS} = -2.5V, I_D = -2A$	50m $\Omega$
$R_{DS(ON)}$ typ. @ $V_{GS} = -1.8V, I_D = -1A$	65m $\Omega$



G : Gate S : Source D : Drain

### Ordering Information

Device	Package	Shipping
KTP2603G	TSOP-6 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel

### Absolute Maximum Ratings (T<sub>A</sub>=25°C)

Parameter	Symbol	Limits	Unit	
Drain-Source Voltage	V <sub>DS</sub>	-20	V	
Gate-Source Voltage	V <sub>GS</sub>	±8		
Continuous Drain Current @ V <sub>GS</sub> =-4.5V, T <sub>A</sub> =25°C	I <sub>D</sub>	-3.9	A	
Continuous Drain Current @ V <sub>GS</sub> =-4.5V, T <sub>A</sub> =70°C		-3.1		
Pulsed Drain Current	I <sub>DM</sub>	-15.6		
Continuous Body Diode Forward Current @ T <sub>A</sub> =25°C	I <sub>S</sub>	-1		
Total Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	1.3	W
		T <sub>A</sub> =70°C	0.8	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55~+150	°C

### Thermal Data

Parameter	Symbol	Steady State	Unit
Thermal Resistance, Junction-to-ambient	R <sub>θJA</sub>	100	°C/W

Note:

- \*a. The value of R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup>FR -4 board with 2 oz. copper, in a still air environment with T<sub>A</sub>=25°C. The power dissipation P<sub>D</sub> is based on R<sub>θJA</sub> and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- \*b. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and low duty cycles to keep initial T<sub>J</sub>=25°C.

**Electrical Characteristics (T<sub>A</sub>=25°C, unless otherwise specified)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
<b>Static</b>					
BV <sub>DSS</sub>	-20	-	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA
V <sub>GS(th)</sub>	-0.4	-	-1.2		V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA
G <sub>FS</sub>	-	9	-	S	V <sub>DS</sub> =-10V, I <sub>D</sub> =-4A
I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V
I <sub>DSS</sub>	-	-	-1	μA	V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V
R <sub>DS(ON)</sub>	-	42	55	mΩ	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A
	-	50	70		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-2A
	-	65	120		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-1A
<b>Dynamic</b>					
C <sub>iss</sub>	-	1150	-	pF	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V, f=1MHz
C <sub>oss</sub>	-	120	-		
C <sub>rss</sub>	-	105	-		
R <sub>g</sub>	-	40	-	Ω	f=1MHz
Q <sub>g</sub> *1, 2	-	14	-	nC	V <sub>DS</sub> =-10V, I <sub>D</sub> =-4A, V <sub>GS</sub> =-4.5V
Q <sub>gs</sub> *1, 2	-	1.7	-		
Q <sub>gd</sub> *1, 2	-	3.5	-		
t <sub>d(ON)</sub> *1, 2	-	5	-	ns	V <sub>DS</sub> =-10V, I <sub>D</sub> =-4A, V <sub>GS</sub> =-4.5V, R <sub>GS</sub> =1Ω
t <sub>r</sub> *1, 2	-	17	-		
t <sub>d(OFF)</sub> *1, 2	-	112	-		
t <sub>f</sub> *1, 2	-	145	-		
<b>Source-Drain Diode</b>					
V <sub>SD</sub> *1	-	-0.85	-1.2	V	I <sub>S</sub> =-4A, V <sub>GS</sub> =0V
t <sub>rr</sub>	-	68	-	ns	I <sub>F</sub> =-2A, dI <sub>F</sub> /dt=100A/μs
Q <sub>rr</sub>	-	62	-	nC	

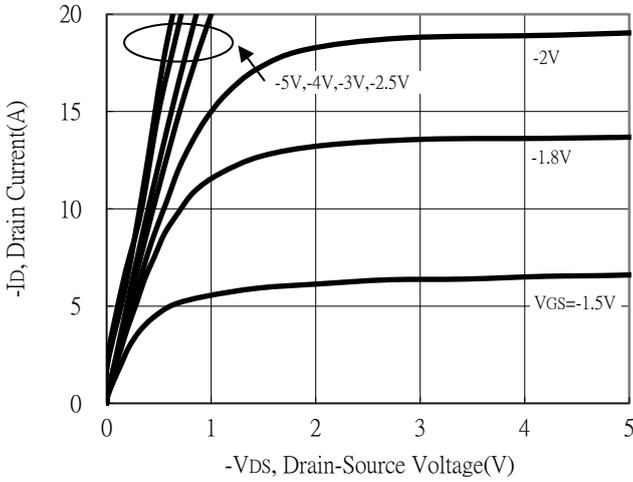
Note:

\*1. Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

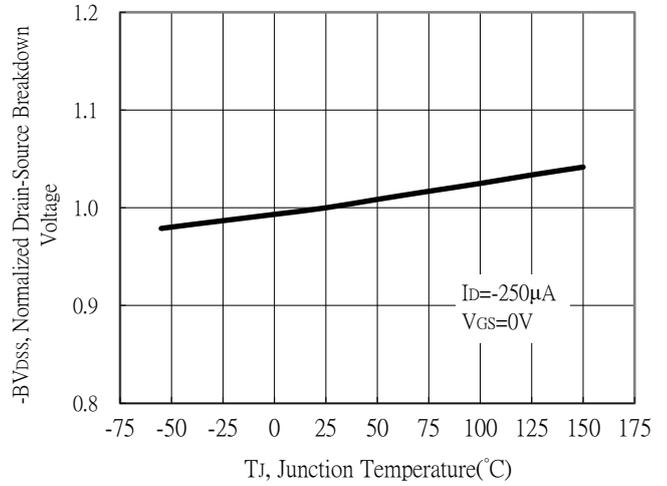
\*2. Independent of operating temperature

**Typical Characteristics**

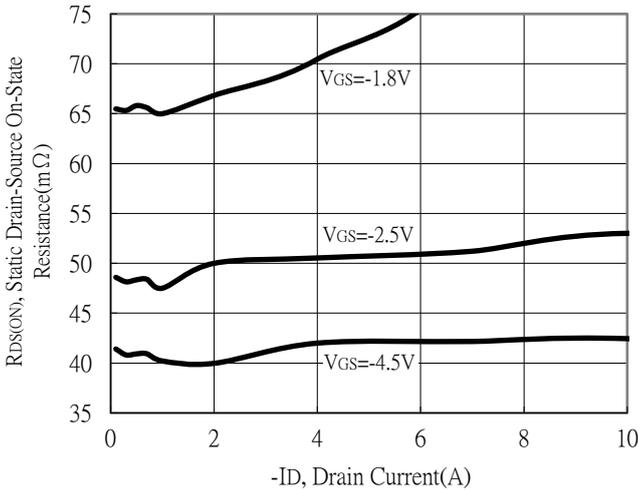
Typical Output Characteristics



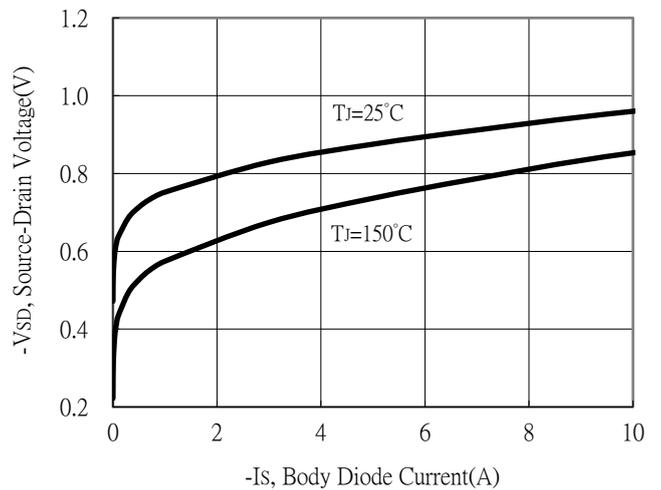
Breakdown Voltage vs Ambient Temperature



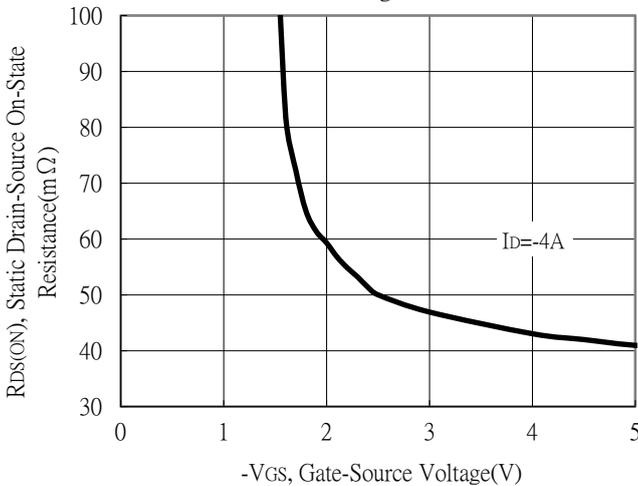
Static Drain-Source On-State resistance vs Drain Current



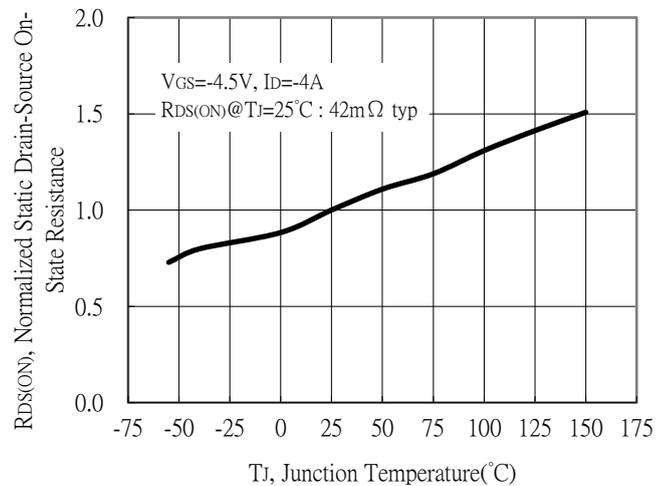
Body Diode Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

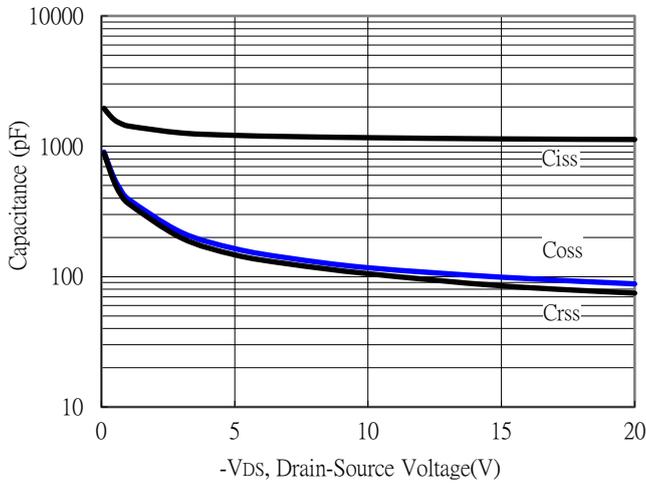


Drain-Source On-State Resistance vs Junction Temperature

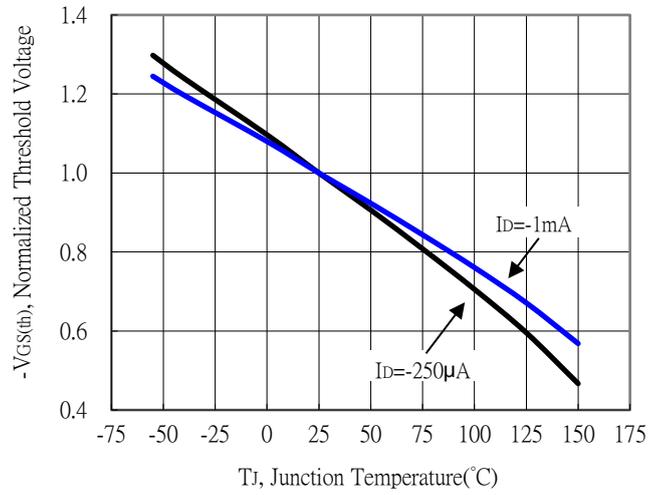


**Typical Characteristics (Cont.)**

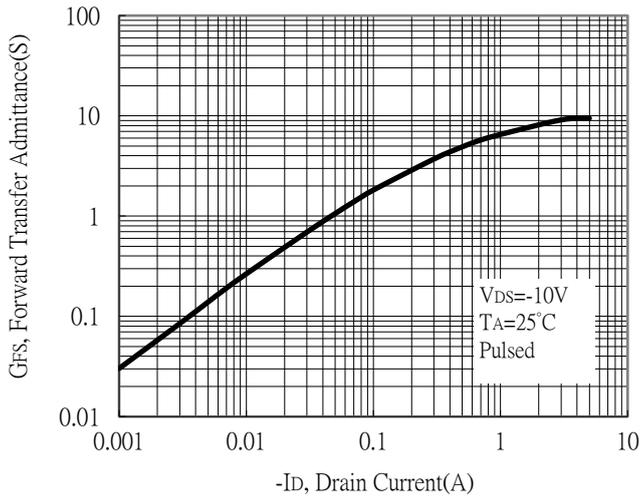
Capacitance vs Drain-to-Source Voltage



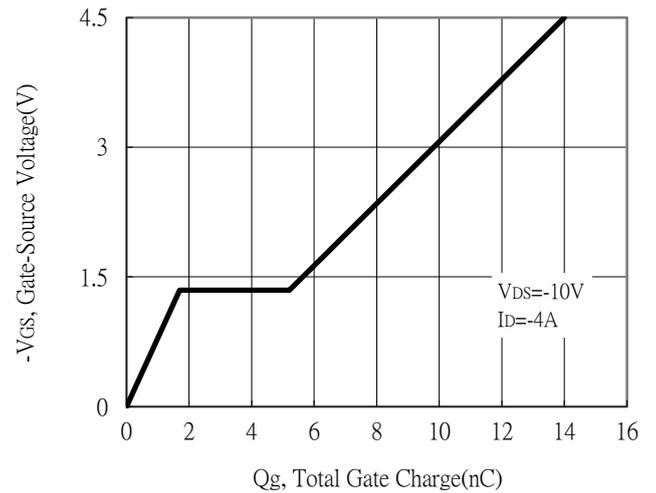
Threshold Voltage vs Junction Temperature



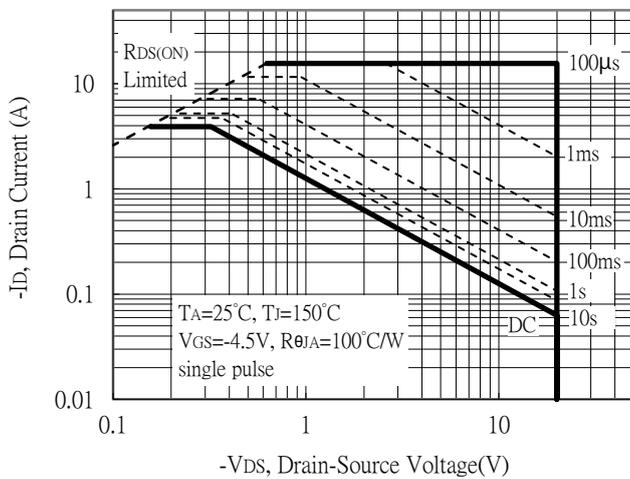
Forward Transfer Admittance vs Drain Current



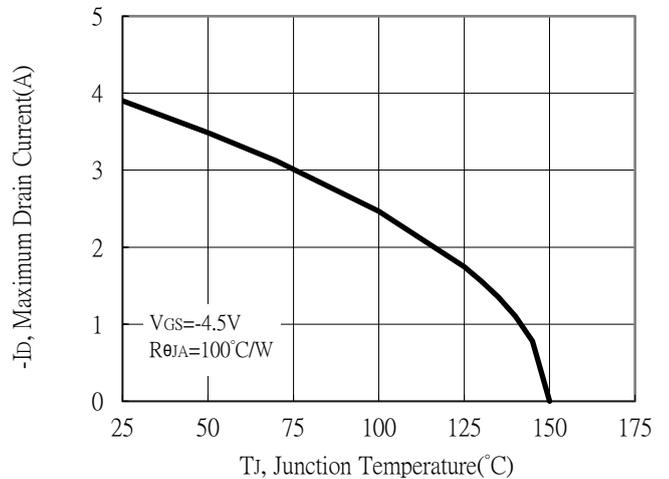
Gate Charge Characteristics



Maximum Safe Operating Area

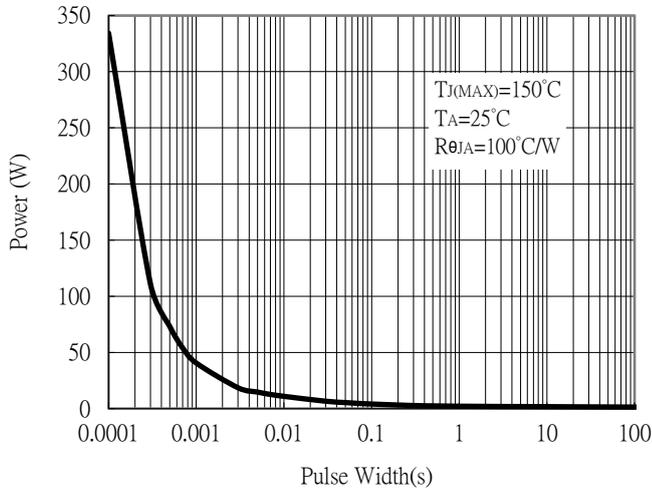


Maximum Drain Current vs Junction Temperature

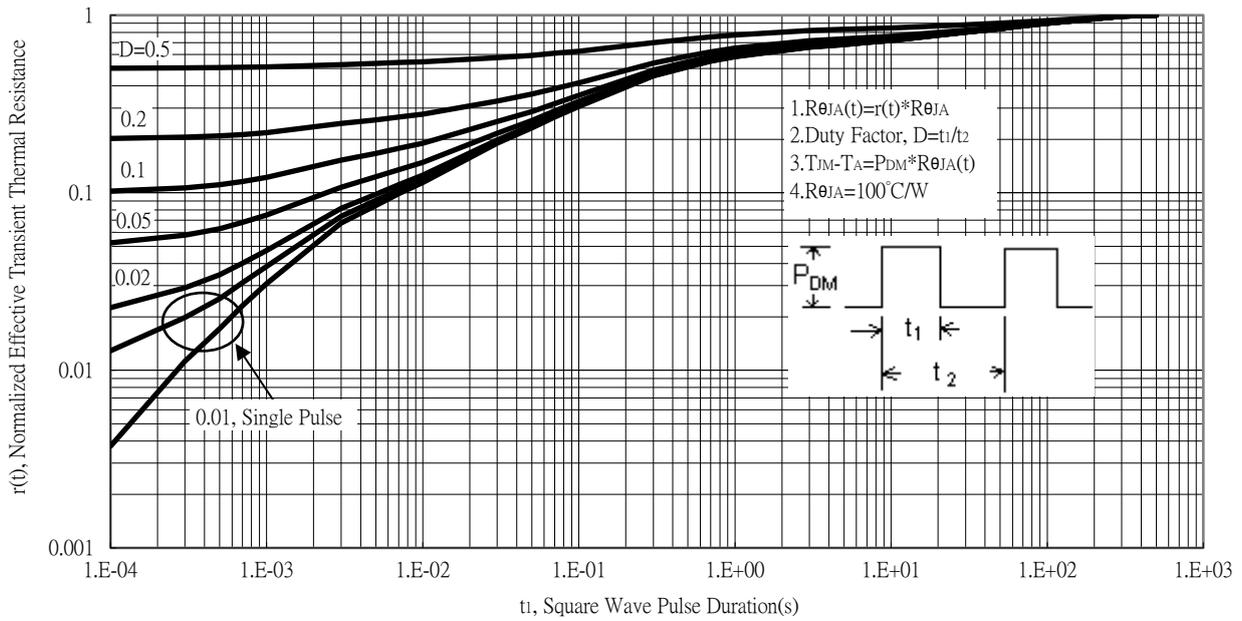


### Typical Characteristics (Cont.)

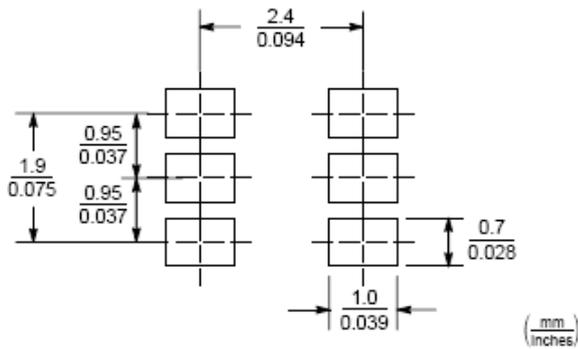
Single Pulse Power Rating, Junction to Ambient



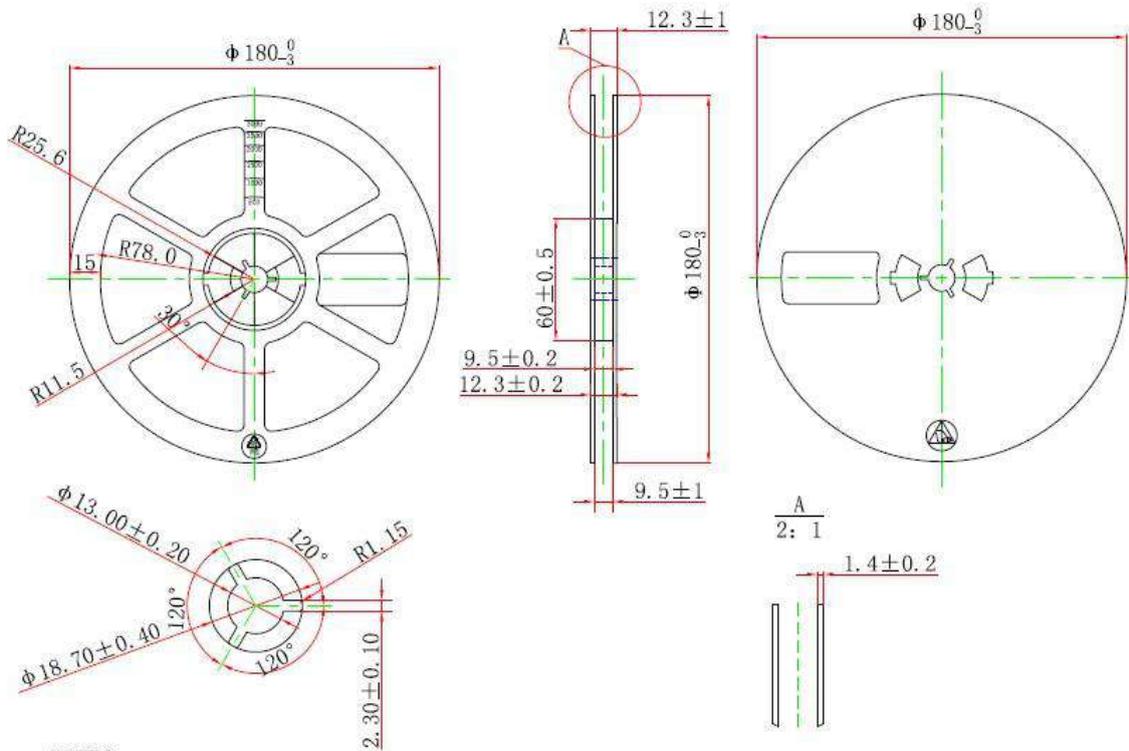
Transient Thermal Response Curves



### Recommended Soldering Footprint

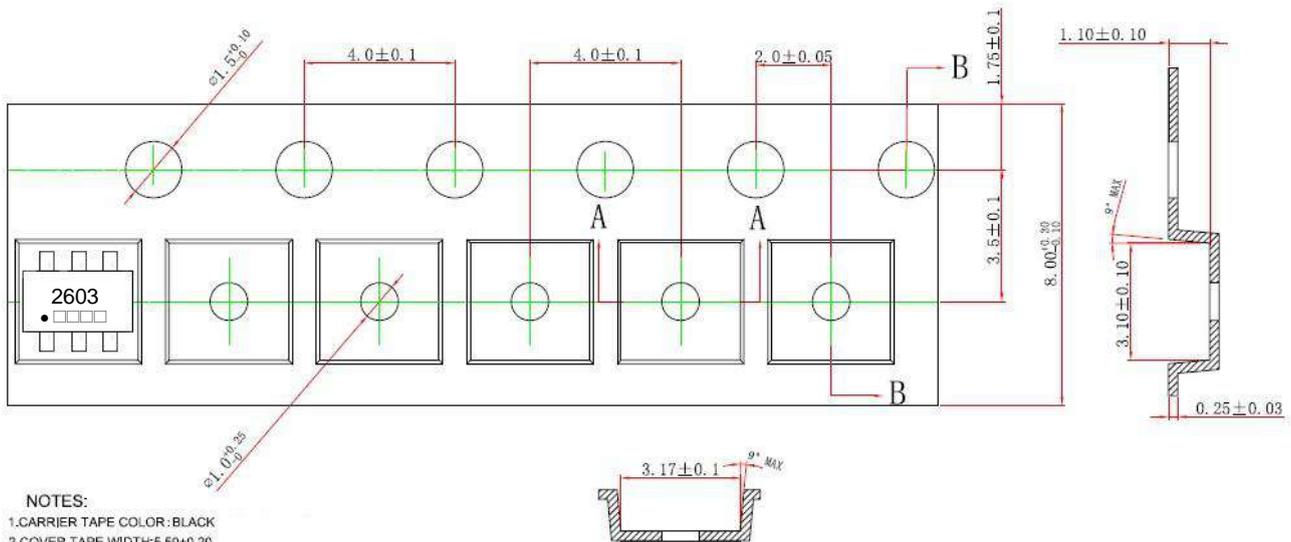


### Reel Dimension



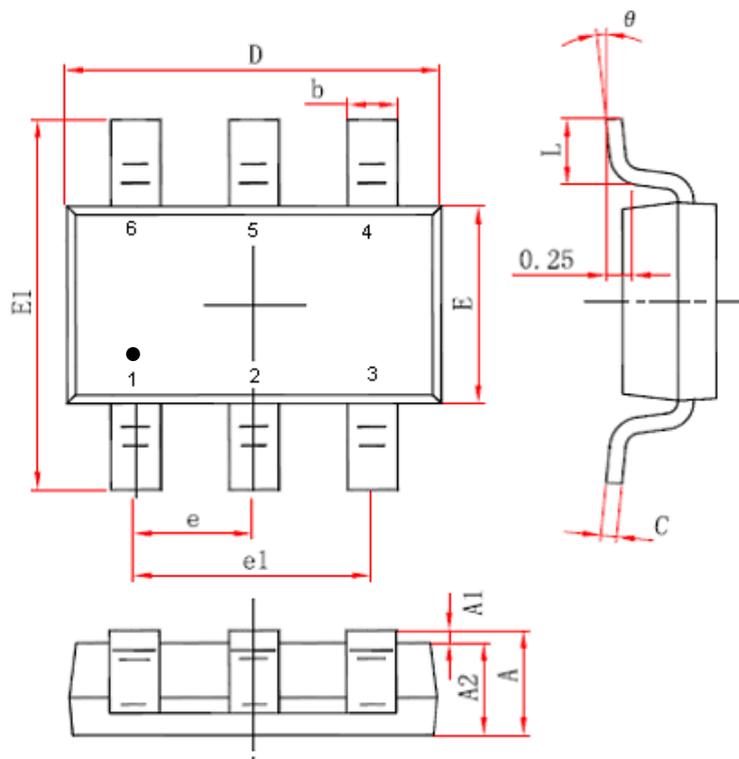
- NOTES:
1. ALL DIM IN mm
  2. ESD-SURFACE RESISTIVITY  $10^5 \sim 10^{11}$  OHMS/SQ
  3. GENERAL TOLERANCE  $\pm 0.25$ :
  4. THE DIRECTION OF VIEW :

### Carrier Tape Dimension



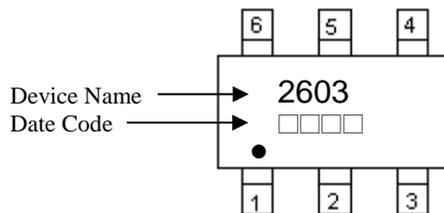
- NOTES:
1. CARRIER TAPE COLOR: BLACK
  2. COVER TAPE WIDTH: 5.50  $\pm 0.20$
  3. COVER TAPE COLOR: TRANSPARENT
  5. ANTISTATIC COATED  $10^5 \sim 10^{10}$  OHMS/SQ.
  6. 10 SPROCKET HOLE PITCH CUMULATIVE TOLERANCE  $\pm 0.20$  MAX.
  7. CAMBER NOT TO EXCEED 1 MM IN 100 MM
  8. ALL DIMS IN mm.
  9. THE DIRECTION OF VIEW :

**TSOP-6 Dimension**



6-Lead TSOP-6 Plastic Surface Mounted Package

Marking:



- Style:
- Pin 1. Drain (D)
  - Pin 2. Drain (D)
  - Pin 3. Gate (G)
  - Pin 4. Source (S)
  - Pin 5. Drain (D)
  - Pin 6. Drain (D)

Date Code(counting from left to right) :  
 1st code: year code, the last digit of Christian year  
 2nd code : month code, Jan→A, Feb→B, Mar→C, Apr→D, May→E, Jun→F, Jul→G, Aug→H, Sep→J, Oct→K, Nov→L, Dec→M  
 3rd and 4th codes : production serial number, 01~99

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035	E	1.600	1.700	0.063	0.067
A1	0.000	0.100	0.000	0.004	E1	2.650	2.950	0.104	0.116
A2	0.700	0.800	0.028	0.031	e	0.95 BSC		0.037 BSC	
b	0.350	0.500	0.014	0.020	e1	1.90 BSC		0.075 BSC	
c	0.080	0.200	0.003	0.008	L	0.300	0.600	0.012	0.024
D	2.820	3.020	0.111	0.119	θ	0°	8°	0°	8°